We claim:

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- A non-photosensitive polyimide precursor composition comprising:
 - a) one or more polyamic acids soluble in *gamma*-butyrolactone (GBL) and aqueous tetramethyl ammonium hydroxide, , and with the proviso that the polyamic acid is also resistant to a solvent used in a photosensitive composition with which the polyimide precursor composition is to be used;
 - b) a solvent comprising gamma-butyrolactone; and

ΙV

c) one or more adhesion promoters selected from the group consisting of the structures described by Formulae I-VI

$$R^{1}$$
 N
 $(CH_{2})n$
 R^{3}
 $R^{5}O$
 OR^{4}
 $R^{5}O$
 OR^{4}
 $R^{5}O$
 OR^{4}
 OR^{5}
 OR^{5}
 OR^{5}
 OR^{4}

I III III R^3 OR4 R^3 OR4 R^3 OR4 R^3 OR4 R^3 OR5

wherein R¹ is selected from the group consisting of H, C₁ –C₁₀ linear, cyclic or branched alkyl, phenyl, halophenyl and alkyl substituted phenyl, R² is selected from the group consisting of C₁ –C₁₀ linear, cyclic or branched alkyl, phenyl, halophenyl

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and alkyl substituted phenyl or one of the following moieties VII, VIII, or IX

- where R³ is C₁ -C₄ linear or branched alkyl or C₁ -C₄ linear or branched alkoxy group, R⁴, R⁵ and R⁶ are independently a C₁ -C₄ linear or branched alkyl group, m is an integer from 1 to about 4, and n is an integer from 1 to about 5.
- 10 2. A composition according to claim 1 wherein the one or more polyamic acids is selected from the group consisting of polyamic acids of the Formula X

where n is an integer ranging from about 5 to about 200 wherein X and Y are independently selected from aromatic and aliphatic moieties which may contain heteroatoms.

 A composition according to claim 2 wherein the one or more polyamic acids of Formula X is one prepared by reacting at least one anhydride monomer of Formula XI with at least one diamine monomer of Formula XII

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and wherein the anhydride monomer is selected from the group consisting of 3,3',4,4'-biphenyltetracarboxylic acid dianhydride, 3.3',4,4' diphenylsulfidetetracarboxylic acid dianhydride. 3,3'4,4'diphenylsulfontetracarboxylic acid dianhydride, 3,3',4,4'-benzophenone tetracarboxylic acid dianhydride, 3,3',4,4'-diphenylmethanetetracarboxylic acid 2,2',3,3' -diphenylmethanetetracarboxylic acid dianhydride, dianhydride, 2,3,3',4'-biphenyltetracarboxylic acid dianhydride, 2,3,3',4'benzophenonetetracarboxylic acid dianhydride, 3,3',4,4'diphenyloxidetetracarboxylic acid dianhydride, 2,3,6,7naphthalenetetracarboxylic acid dianhydride, 1,4,5,7naphtnalenetetracarboxylic acid dianhydride, 2,2-bis(3,4dicarboxyphenyl)propane dianhydride, 2,2-bis(2,3-dicarboxyphenyl)propane 2,2-bis(3,4-dicarboxyphenyl)hexafluoropropane dianhydride, dianhydride, 1,3-diphenylhexafluoropropane-3,3,4,4-tetracarboxylic acid dianhydride, 1,4,5,6naphthalenetetracarboxylic dianhydride, 2.2',3,3'diphenyltetracarboxylic acid dianhydride, 3,4,9,10-perylenetetracarboxylic acid dianhydride, 1,2,4,5 naphthalenetetracarboxylic acid dianhydride. 1,4,5,8-naphthalenetetracarboxylic acid dianhydride. 1,8,9,10phenanthrenetetracarboxylic acid dianhydride. 1,1-bis(2,3dicarboxyphenyl)ethane dianhydride, 1,1-bis(3,4-dicarboxyphenyl)ethane dianhydride, 1,2,3,4-benzenetetracarboxylic acid dianhydride and 1,2,4,5benzenetetracarboxylic acid dianhydride, and the diamine monomer is selected from the group consisting of 5(6)-amino-1-(4-aminophenyl)-1,3,3trimethylindane, *m*-phenylenediamine. p-phenylenediamine. 2,2'bis(trifluoromethyl)-4,4'-diamino-1,1'-biphenyl, 3,4'-diaminodiphenyl ether. 4,4'-diaminodiphenyl ether, 3,3'-diaminodiphenyl ether, 2,4-tolylenediamine,

3,3'-diaminodiphenyl sulfone, 3,4'-diaminodiphenyl sulfone, 4,4'diaminodiphenyl sulfone. 3,3'-diaminodiphenylmethane. 4,4'diaminodiphenylmethane, 3.3'-diaminodiphenylmethane, 3,4'diaminodiphenylmethane, 4,4'-diaminodiphenyl ketone, 3,3'-diaminodiphenyl ketone, 3,4'-diaminodiphenyl ketone, 1,3-bis (4-aminophenoxy) benzene, 1,3-5 bis(3-amino-phenoxy) benzene, 1,4-bis (γ -aminopropyl)tetramethyldisiloxane, 2,3,5,6-tetramethyl-p-phenylenediamine, *m*-xylylenediamine, pxylylenediamine, methylenediamine. tetramethylenediamine, pentamethylenediamine, hexamethylenediamine. dimethylhexamethylenediamine, 10 3-methoxyhexamethylenediamine, heptamethylenediamine, 2,5-dimethylheptamethylenediamine, 3methylheptamethylenediamine, 4,4-dimethylheptamethylenediamine, octamethylenediamine. nonamethylenediamine. 2.5dimethylnonamethylenediamine, decamethylenediamine, ethylenediamine, 15 propylenediamine. 2,2-dimethylpropylenediamine, 1,10-diamino-1,10dimethyldecane, 2,11-diaminidodecane, 1,12-diaminooctadecane, 2,17diaminoeicosane, 3,3'-dimethyl-4,4'-diaminodiphenylmethane, bis(4aminocyclohexyl)methane, bis(3-aminonorbornyl)methane, 3,3'diaminodiphenylethane, 4,4'-diaminodiphenylethane, and 4,4'diaminodiphenyl sulfide, 2,6-diaminopyridine, 2,5-diaminopyridine, 20 2,6diamino-4-trifluoromethylpyridine, 2,5-diamino-1,3,4,-oxadiazole, 1.4diaminocyclohexane, piperazine, 4,4'-methylenedianiline, 4,4'-methylenebis(o-choloroaniline). 4,4'-methylene-bis(3-methylaniline), 4,4'-methylenebis(2-ethylaniline), 4,4'-methylene-bis(2-methoxyaniline), 4,4'-oxy-dianiline, 25 4,4'-oxy-bis-(2-methoxyaniline), 4,4'-oxy-bis-(2-chloroaniline), 4.4'-thiodianiline, 4,4'-thio-bis-(2-methylaniline), 4,4'-thio-bis-(2-methyoxyaniline), 4,4'thio-bis-(2-chloroaniline), 3,3'sulfonyl-dianiline, and 3,3'sulfonyl-dianiline.

A composition according to claim 3 wherein the anhydride monomer is

selected from the group consisting of a compound selected from the group consisting of compounds described by the structures (XIII - XV):

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Z XIII

Z-

ΧV

where Z= is selected from the group consisting of -O-, -S-, -C(CF₃)₂-, -CH₂-, -SO₂-, -NHCO- or -Si(R)₂- where R' is a linear, branched or cyclic alkyl group containing from 1 to 8 carbon atoms.

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5. A composition according to claim 4 wherein the diamine monomer is at least one compound having the structure XVI

where W= is selected from the group consisting of -O-, -S-, -C(CF₃)₂-, -CH₂-, -SO₂-, -NHCO- and $-Si(R')_2$ - where R' is a linear branched or cyclic alkyl group containing from 1 to 8 carbon atoms.

- 5 6. A composition according to claim 5 wherein Z is -O- and W is -O-.
- 7. A composition according to claim 3 wherein the one or more polyamic acids is a polyamic acid selected from the group consisting of those from a polyamic acid from 4,4'-diaminodiphenyl ether and 3,3',4,4'diphenyloxidetetracarboxylic acid dianhydride, a polyamic acid polymer from 10 4,4'-diaminodiphenyl ether and a mixture of 95-85% of 3,3',4,4'diphenyloxidetetracarboxylic acid dianhydride and 5-15% of another anhydride of Formula XI.
- A composition according to claim 2 wherein the ratio of diamine to dianhydride units in the polyamic acid of Formula X is from about 0.9 to about
 1.
- 9. A composition according to claim 1 wherein the % of polyamic acid in the composition is from about 6 to about 23 % by weight of the composition.
 - A composition according to claim 1 wherein the % of polyamic acid in the composition is from about 12 to about 22 % by weight of the composition.
- A composition according to claim 10 wherein the solvent comprise from about74% to about 92% by weight of the composition.
 - 12. A composition according to claim 11 wherein the composition contains at

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least one cosolvent having a boiling point of between about 110 °C and about 230 °C.

- 13. A composition according to claim 12 wherein the cosolvent is selected from the group consisting of *gamma*-valerolactone, *gamma*-caprolactone, *delta*-valerolactone, 2-hexanone, 3-hexanone, 3-heptanone, and 4-methyl -2-pentanone.
- 14. A composition according to claim 1 wherein the adhesion promoter is one selected from those of the Formulae I, II, IV and V.
 - 15. A composition according to claim 1 wherein the adhesion promoter is one of Formula I wherein R¹ and R² are each independently C₁–C₁₀ linear, cyclic or branched alkyl or one of R¹ and R² is phenyl.
 - 16. A composition according to claim 1 wherein the adhesion promoter is selected from the group consisting of those of Formulae XVII, XVIII, XIX, and XX

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XVII

O

Si(OMe)₃

$$H_2C$$

Si(OEt)₃

XIX

HS

Si(OMe)₃

XXX.

- 17. A composition according to claim 1 wherein the adhesion promoter comprises from about 0.05% to about 1.5% by weight of the composition.
- 30 18. A process for producing a patterned polyimide structure on a substrate, the process comprising the steps of:

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- (a) providing a substrate;
- (b) in a first coating step, coating the substrate with a non-photosensitive polyimide precursor composition of claim 1;
- (c) baking the layer of non-photosensitive polyimide precursor composition at a temperature or temperatures below 140 °C;
- (d) in a second coating step, coating a layer of a photoresist over the layer of non-photosensitive polyimide precursor composition to form a bilayer coating;
- (e) exposing the bilayer coating to radiation suitable appropriate for the photoresist;
- (f) developing the bilayer coatings with one or more aqueous developers;
- (g) removing the remaining photoresist layer; and
- (h) curing the non-photosensitive polyimide precursor composition layer at a temperature at least about 200 °C to produce a polyimide structure.
- 19. A process according to claim 18 wherein the one or more polyamic acids in the non-photosensitive polyimide precursor composition is selected from the group consisting of polyamic acids of the Formula X

where n is an integer ranging from about 5 to about 200 wherein **X** and **Y** are independently selected from aromatic and aliphatic moieties which may contain heteroatoms.

20. A process according to claim 19 wherein the one or more polyamic acids of Formula X is one prepared by reacting at least one anhydride monomer of Formula XI with at least one diamine monomer of Formula XII

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and wherein the anhydride monomer is selected from the group consisting of 3,3',4,4'-biphenyltetracarboxylic acid dianhydride. 3,3',4,4' diphenylsulfidetetracarboxylic acid dianhydride, 3,3'4,4'diphenylsulfontetracarboxylic acid dianhydride, 3,3',4,4'-benzophenone tetracarboxylic acid dianhydride, 3,3',4,4'-diphenylmethanetetracarboxylic acid 2,2',3,3' -diphenylmethanetetracarboxylic acid dianhydride, dianhydride. 2,3,3',4'-biphenyltetracarboxylic acid dianhydride, 2,3,3',4'benzophenonetetracarboxylic acid dianhydride, 3,3',4,4'diphenyloxidetetracarboxylic acid dianhydride, 2,3,6,7naphthalenetetracarboxylic acid dianhydride, 1,4,5,7naphtnalenetetracarboxylic acid dianhydride. 2,2-bis(3,4dicarboxyphenyl)propane dianhydride, 2,2-bis(2,3-dicarboxyphenyl)propane 2,2-bis(3,4-dicarboxyphenyl)hexafluoropropane dianhydride, 1,3-diphenylhexafluoropropane-3,3,4,4-tetracarboxylic acid dianhydride. 1.4.5.6naphthalenetetracarboxylic dianhydride. 2,2',3,3'diphenyltetracarboxylic acid dianhydride, 3,4,9,10-perylenetetracarboxylic acid dianhydride, 1,2,4,5 naphthalenetetracarboxylic acid dianhydride. 1,4,5,8-naphthalenetetracarboxylic acid dianhydride, 1,8,9,10phenanthrenetetracarboxylic acid dianhydride. 1,1-bis(2,3dicarboxyphenyl)ethane dianhydride. 1,1-bis(3,4-dicarboxyphenyl)ethane dianhydride, 1,2,3,4-benzenetetracarboxylic acid dianhydride and 1,2,4,5-

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benzenetetracarboxylic acid dianhydride, and the diamine monomer is selected from the group consisting of 5(6)-amino-1-(4-aminophenyl)-1,3,3trimethylindane. *m*-phenylenediamine. p-phenylenediamine, bis(trifluoromethyl)-4,4'-diamino-1,1'-biphenyl, 3,4'-diaminodiphenyl ether, 4,4'-diaminodiphenyl ether, 3,3'-diaminodiphenyl ether, 2,4-tolylenediamine, 5 3,3'-diaminodiphenyl sulfone, 3,4'-diaminodiphenyl sulfone, 4.4'diaminodiphenyl sulfone, 3,3'-diaminodiphenylmethane, 4.4'diaminodiphenylmethane, 3,3'-diaminodiphenylmethane, 3,4'diaminodiphenylmethane, 4,4'-diaminodiphenyl ketone, 3,3'-diaminodiphenyl ketone, 3,4'-diaminodiphenyl ketone, 1,3-bis (4-aminophenoxy) benzene, 1,3bis(3-amino-phenoxy) benzene, 1,4-bis (γ -aminopropyl)tetramethyldisiloxane, 2,3,5,6-tetramethyl-p-phenylenediamine, m-xylylenediamine, xylylenediamine. methylenediamine. tetramethylenediamine, pentamethylenediamine, hexamethylenediamine, 2,5dimethylhexamethylenediamine, 3-methoxyhexamethylenediamine. heptamethylenediamine. 2,5-dimethylheptamethylenediamine, 3methylheptamethylenediamine, 4,4-dimethylheptamethylenediamine, octamethylenediamine, nonamethylenediamine, 2.5dimethylnonamethylenediamine, decamethylenediamine, ethylenediamine, propylenediamine, 2,2-dimethylpropylenediamine, 1,10-diamino-1,10dimethyldecane, 2,11-diaminidodecane, 1,12-diaminooctadecane, 2,17diaminoeicosane. 3,3'-dimethyl-4,4'-diaminodiphenylmethane, bis(4aminocyclohexyl)methane, bis(3-aminonorbornyl)methane, 3.3'diaminodiphenylethane, 4,4'-diaminodiphenylethane, and 4,4'diaminodiphenyl sulfide, 2,6-diaminopyridine, 2,5-diaminopyridine, 2,6diamino-4-trifluoromethylpyridine, 2,5-diamino-1,3,4,-oxadiazole, 1.4diaminocyclohexane, piperazine, 4,4'-methylenedianiline, 4,4'-methylenebis(o-choloroaniline), 4,4'-methylene-bis(3-methylaniline), 4,4'-methylenebis(2-ethylaniline), 4,4'-methylene-bis(2-methoxyaniline), 4,4'-oxy-dianiline, 4,4'-oxy-bis-(2-methoxyaniline), 4,4'-oxy-bis-(2-chloroaniline), 4.4'-thio-

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dianiline, 4,4'-thio-bis-(2-methylaniline), 4,4'-thio-bis-(2-methyoxyaniline), 4,4'-thio-bis-(2-chloroaniline), 3,3'sulfonyl-dianiline, and 3,3'sulfonyl-dianiline.

21. A process according to claim 20 wherein the anhydride monomer is selected from the group consisting of a compound selected from the group consisting of compounds described by the structures (XIII - XV):

where Z= is selected from the group consisting of -O-, -S-, -C(CF₃)₂-, -CH₂-, -SO₂-, -NHCO- or -Si($R^{'}$)₂- where $R^{'}$ is a linear, branched or cyclic alkyl group containing from 1 to 8 carbon atoms.

22. A process according to claim 21 wherein the diamine monomer is at least one compound having the structure XVI

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where W= is selected from the group consisting of -O-, -S-, -C(CF₃)₂-, -CH₂-, -SO₂-, -NHCO- and -Si(R['])₂- where R' is a linear branched or cyclic alkyl group containing from 1 to 8 carbon atoms.

- 5 23, A process according to claim 22 wherein Z is -O- and W is -O-.
- 24. A process according to claim 20 wherein the one or more polyamic acids is a polyamic acid s elected from the group consisting of those from a polyamic acid from 4,4'-diaminodiphenyl ether and 3,3',4,4'-diphenyloxidetetracarboxylic acid dianhydride, a polyamic acid polymer from 4,4'-diaminodiphenyl ether and a mixture of 95-85% of 3,3',4,4'-diphenyloxidetetracarboxylic acid dianhydride and 5-15% of another anhydride of Formula XI.
- 15 25. A process according to claim 19 wherein the ratio of diamine to dianhydride units in the polyamic acid of Formula X is from about 0.9 to about 1.
 - 26. A process according to claim 18 wherein the % of polyamic acid in the composition is from about 6 to about 23 % by weight of the composition.
 - 27. A process according to claim 18 wherein the % of polyamic acid in the composition is from about 12 to about 22 % by weight of the composition.
- 28. A process according to claim 27 wherein the solvent comprise from about 74% to about 92% by weight of the composition.
 - 29. A process according to claim 28 wherein the composition contains at least one cosolvent having a boiling point of between about 110 °C and about 230

°C.

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- 30. A process according to claim 29 wherein the cosolvent is selected from the group consisting of *gamma*-valerolactone, *gamma*-caprolactone, *delta*-valerolactone, 2-hexanone, 3-hexanone, 3-heptanone, and 4-methyl -2-pentanone.
- 31. A process according to claim 18 wherein the adhesion promoter is one selected from those of the Formulae I, II, IV and V.
- 32. A process according to claim 18 wherein the adhesion promoter is one of Formula I wherein R¹ and R² are each independently C₁–C₁₀ linear, cyclic or branched alkyl or one of R¹ and R² is phenyl.
- 15 33. A process according to claim 18 wherein the adhesion promoter is selected from the group consisting of those of Formulae XVII, XVIII, XIX, and XX

$$XVII$$

O

Si(OMe)₃
 H_2C

Si(OEt)₃

XIX

HS

Si(OMe)₃

XXX.

- A process according to claim 18 wherein the adhesion promoter comprises from about 0.05% to about 1.5% by weight of the composition.
 - 35. A process according to claim 18 wherein in step c) the baking occurs at a temperature or temperatures below 130°.
 - 36. A patterned polyimide structure on a substrate produced according to the

process of claim 18.